

LOW DROP-OUT 5V DUAL VOLTAGE REGULATOR

- OUTPUT CURRENT OF BOTH REGULATORS : 100 mA GUARANTEED
- INTERNAL SHORT-CIRCUIT AND THERMAL PROTECTION
- FIRST REGULATOR OUTPUT : LOW DISCHARGE CURRENT
- SECOND REGULATOR OUTPUT : SWITCHED-OFF WITH ACTIVE DISCHARGE
- RESET OUTPUT WITH ADJUSTABLE PULSE WIDTH

DESCRIPTION

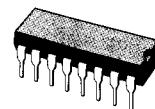
The TEA5110 is a dual positive 5V voltage regulator specially designed to supply a microprocessor and associated circuits.

The first regulator supplies the microprocessor in normal operating conditions. In standby mode, the regulator has a very high output impedance (current drain less than 1 μ A) and the microprocessor may be powered by a battery.

The second regulator supplies the peripherals and provides a halt signal to the microprocessor to turn it in standby mode.

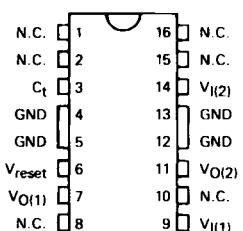
The circuit generates a reset pulse when :

- the supply voltage is applied to the circuit and the output of the second regulator is at its nominal value, and
- when the output of the second regulator is at its nominal value again after a shut-down on the output of the first regulator (see figure 2 page 4).



TEA5110
 BATWING DIP16
 (Plastic Package)

PIN CONNECTIONS



E88TEA5110-01

- | | |
|-----------------|---------------------------|
| 1 - N.C. | |
| 2 - N.C. | |
| 3 - C_t | : Time constant capacitor |
| 4 - GND | : Ground |
| 5 - GND | : Ground |
| 6 - V_{reset} | : Reset output |
| 7 - $V_{O(1)}$ | : Output voltage 1 |
| 8 - N.C. | |
| 9 - $V_{I(1)}$ | : Input voltage |
| 10 - N.C. | |
| 11 - $V_{O(2)}$ | : Output voltage 2 |
| 12 - GND | : Ground |
| 13 - GND | : Ground |
| 14 - $V_{I(2)}$ | : Input voltage 2 |
| 15 - N.C. | |
| 16 - N.C. | |

ABSOLUTE MAXIMUM RATINGS

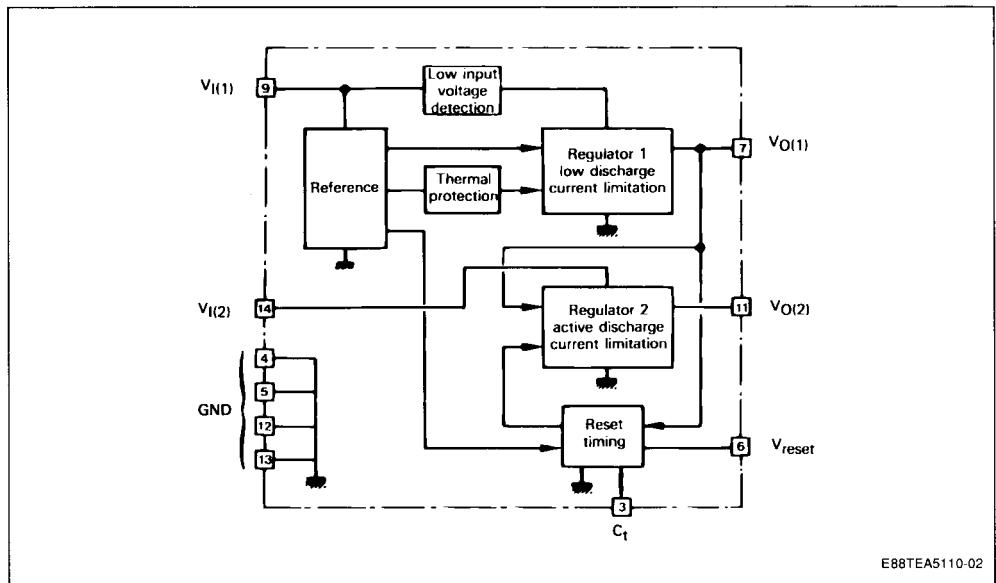
Symbol	Parameter	Value	Unit
V_I	Input Voltage	20	V
I_O	Output Current	Internally Limited	A
P_{tot}	Power Dissipation	Internally Limited	W
T_{oper}	Operating Ambient Temperature Range	0 to 70	°C
T_{stg}	Storage Temperature Range	- 65 to 150	°C

THERMAL DATA

$R_{th(j-a)}^*$	Junction-ambient Thermal Resistance	45	°C/W
$R_{th(j-c)}$	Junction-case Thermal Resistance	11	°C/W

* The $R_{th(j-a)}$ is measured on devices soldered on 35 μm thick copper surface of 40 cm².

BLOCK DIAGRAM



E88TEA5110-02

ELECTRICAL CHARACTERISTICS $T_j = +25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit
$V_{O(1)}$	Output Voltage (+ 7 V $\leq V_I \leq + 18$ V, 0 $\leq I_{O(1)} \leq 100$ mA)	4.9	5.05	5.2	V
$V_{O(2)}$	Output Voltage (+ 7 V $\leq V_I \leq + 18$ V, 0 $\leq I_{O(2)} \leq 100$ mA)	4.8	5	5.2	V
$V_{O(1)} - V_{O(2)}$	Output Voltage Difference + 7 V $\leq V_I \leq + 18$ V, 0 $\leq I_{O(1)} \leq 100$ mA, 0 $\leq I_{O(2)} \leq 100$ mA	0	50	100	mV
$K_{VI(1)}$ $K_{VI(2)}$	Line Regulation + 6.8 V $\leq V_I \leq + 18$ V, $I_{O(1)} = 50$ mA + 6.8 V $\leq V_I \leq + 18$ V, $I_{O(2)} = 50$ mA		10 20	50 50	mV mV
$K_{VO(1)}$ $K_{VO(2)}$	Load Regulation 5 mA $\leq I_{O(2)} \leq 100$ mA, $V_I = + 10$ V 5 mA $\leq I_{O(2)} \leq 100$ mA, $V_I = + 10$ V		10 20	50 50	mV mV
I_Q	Quiescent Current (+ 6.8 V $\leq V_I \leq + 18$ V, $I_{Q(1)} = I_{Q(2)} = 0$)		6	8	mA
$I_{SC(1)}$ $I_{SC(2)}$	Short-circuit Current $V_I = + 10$ V, 0 $\leq V_{O(1)} \leq + 5$ V $V_I = + 10$ V, 0 $\leq V_{O(2)} \leq + 5$ V		200 200		mA mA
$V_I - V_{O(1)}$	Minimum Dropout Voltage - (note 1) Output 1 $I_{O(1)} = 0$ $I_{O(1)} = 0.1$ A		1.4 1.6		V V
$V_I - V_{O(2)}$	Output 2 $I_{O(2)} = 0$ $I_{O(2)} = 0.1$ A		1.5 1.7		V V
$I_{dis(1)}$	$V_{O(1)}$ Discharge Current ($V_I = 0$, $V_{O(1)} = + 5$ V)			1	µA
	Minimum Input Voltage to Switch on $V_{O(2)}$ Output (fig. 1, note 2)	$(V_{O1} + 1.4)$	$(V_{O1} + 1.6)$	$(V_{O1} + 1.8)$	V
ΔV_{IL}	Input Hysteresis to Switch off $V_{O(2)}$ Output (fig. 1)	200	300	400	mV
	Minimum $V_{O(1)}$ Output Voltage to Switch on $V_{O(2)}$	4.5	4.6	4.7	V
$\Delta V_{C(1)}$	$V_{O(1)}$ Hysteresis Voltage to switch off $V_{O(2)}$ (fig. 2)	30	50	70	mV
$V_{L(02)}$	$V_{O(2)}$ Low Output Voltage (active discharge) $V_I = + 10$ V, $I_{O(2)} = - 90$ mA $V_I = + 10$ V, $I_{O(2)} = - 10$ mA		1.3 120	1.6 180	V mV
$V_{L(reset)}$	Reset Low Output Voltage ($V_I = + 10$ V, $I_{reset1} = - 16$ mA)		120	400	mV
$V_{H(reset)}$	Reset High Output Voltage ($V_I = + 10$ V, $I_{reset} = 1$ mA)	$V_{O(2)} - 1$ V		$V_{O(2)}$	V
t_{reset}	Reset Pulse Duration ($V_I = + 10$ V, $C_{reset} = 10$ nF) – Note 3	4	8	16	ms
KVT	Average Temperature Coefficient of Output Voltage ($T_j = 0^\circ\text{C}$ to -70°C)		0.5		mV/°C
θ	Thermal Shut Down Temperature	110			°C
SVR	Supply Voltage Rejection Ratio $V_I = + 12$ V, $\Delta V_I = 4$ Vpp, $I_O = 10$ mA, $f = 100$ Hz		50		dB

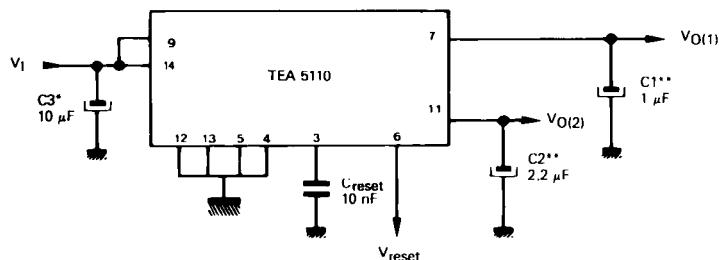
Notes : 1. The dropout voltage (input-output voltage difference) is measured when the output voltage has dropped 100 mV from the nominal value obtained at 10 V input voltage.

Dropout voltage is dependent upon load current and junction temperature.

2. $V_{O(1)}$ voltage is measured at 10 V input voltage.

3. t_{reset} (ms) = 0.8 C_{reset} (nF).

Figure 1 : Typical Application and Test Circuit.

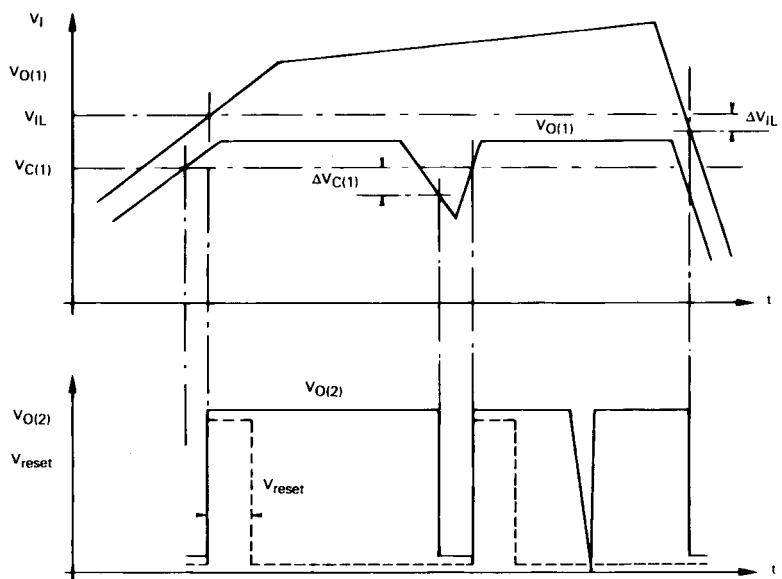


C1, C2, C3 solid tantalum capacitors.

* Required when the circuit is far from power supply capacitors.

** Required for current limitation stability.

E88TEA5110-03

Figure 2 : Dynamic Characteristics of V_{O(1)}, V_{O(2)}, V_{reset} Outputs.

PACKAGE MECHANICAL DATA

16 PINS – PLASTIC DIP

